CLAIMS

1. A substrate dividing method comprising the steps of:

irradiating a substrate with laser light while positioning a light-converging point within the substrate, so as to form a modified region due to multiphoton absorption within the substrate, and causing the modified region to form a starting point region for cutting along a line along which the substrate should be cut in the substrate inside by a predetermined distance from a laser light incident face of the substrate; and

grinding the substrate after the step of forming the starting point region for cutting such that the substrate attains a predetermined thickness.

2. A substrate dividing method according to claim 1, wherein the substrate is a semiconductor substrate.

3. A substrate dividing method according to claim 2, wherein the modified region is a molten processed region.

4. A substrate dividing method according to claim 1, wherein the substrate is an insulating substrate.

5. A substrate dividing method according to one of claims 1 to 4, wherein a front face of the substrate is formed with a functional device; and

wherein a rear face of the substrate is ground in the step of grinding the substrate.

6. A substrate dividing method according to claim 5, wherein the step of grinding the substrate includes a step of

subjecting the rear face of the substrate to chemical etching.